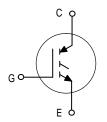
## Designer's™ Data Sheet

# **Insulated Gate Bipolar Transistor**

### N-Channel Enhancement-Mode Silicon Gate

This Insulated Gate Bipolar Transistor (IGBT) uses an advanced termination scheme to provide an enhanced and reliable high voltage–blocking capability. Short circuit rated IGBT's are specifically suited for applications requiring a guaranteed short circuit withstand time such as Motor Control Drives. Fast switching characteristics result in efficient operation at high frequencies.

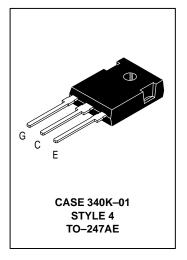
- Industry Standard High Power TO–247 Package with Isolated Mounting Hole
- High Speed E<sub>off</sub>: 150 μJ/A typical at 125°C
- High Short Circuit Capability 10 μs minimum
- Robust High Voltage Termination



### MGW12N120

Motorola Preferred Device

IGBT IN TO-247
12 A @ 90°C
20 A @ 25°C
1200 VOLTS
SHORT CIRCUIT RATED



### **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Collector–Emitter Voltage	VCES	1200	Vdc	
Collector–Gate Voltage (R <sub>GE</sub> = 1.0 MΩ)	V <sub>CGR</sub>	1200	Vdc	
Gate-Emitter Voltage — Continuous	V <sub>GE</sub>	±20	Vdc	
Collector Current — Continuous @ T <sub>C</sub> = 25°C — Continuous @ T <sub>C</sub> = 90°C — Repetitive Pulsed Current (1)	IC25 IC90 ICM	20 12 40	Adc Apk	
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	125 0.98	Watts W/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	
Short Circuit Withstand Time ( $V_{CC}$ = 720 Vdc, $V_{GE}$ = 15 Vdc, $T_J$ = 125°C, $R_G$ = 20 $\Omega$ )	t <sub>SC</sub>	10	μs	
Thermal Resistance — Junction to Case – IGBT — Junction to Ambient	R <sub>θ</sub> JC R <sub>θ</sub> JA	1.0 45	°C/W	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	TL	260	°C	
Mounting Torque, 6–32 or M3 screw	10 lbf•in (1.13 N•m)			

<sup>(1)</sup> Pulse width is limited by maximum junction temperature. Repetitive rating.

**Designer's Data for "Worst Case" Conditions** — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

Designer's is a trademark of Motorola, Inc.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 2



### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

Cha	racteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		-				
Collector–to–Emitter Breakdown Voltage (VGE = 0 Vdc, I <sub>C</sub> = 25 μAdc) Temperature Coefficient (Positive)		V <sub>(BR)</sub> CES	1200 —	 870	_	Vdc mV/°C
Emitter-to-Collector Breakdown Voltage (V <sub>GE</sub> = 0 Vdc, I <sub>EC</sub> = 100 mAdc)		V(BR)ECS	25	_	_	Vdc
Zero Gate Voltage Collector Current (VCE = 1200 Vdc, VGE = 0 Vdc) (VCE = 1200 Vdc, VGE = 0 Vdc, TJ = 125°C)		ICES	_	_	100 2500	μAdc
Gate-Body Leakage Current (VGE = ± 20 Vdc, VCE = 0 Vdc)		IGES	_	_	250	nAdc
ON CHARACTERISTICS (1)		•				
Collector-to-Emitter On-State Volta (VGE = 15 Vdc, I <sub>C</sub> = 5.0 Adc) (VGE = 15 Vdc, I <sub>C</sub> = 5.0 Adc, T <sub>J</sub> (VGE = 15 Vdc, I <sub>C</sub> = 10 Adc)		VCE(on)	_ _ _	2.51 2.36 3.5	3.37 — 4.42	Vdc
Gate Threshold Voltage (V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 1.0 mAdc) Threshold Temperature Coefficien	nt (Negative)	VGE(th)	4.0 —	6.0 10	8.0 —	Vdc mV/°C
Forward Transconductance (V <sub>CE</sub> =	: 10 Vdc, I <sub>C</sub> = 10 Adc)	9fe	_	12	_	Mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V <sub>CE</sub> = 25 Vdc, V <sub>GE</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>ies</sub>	_	930	_	pF
Output Capacitance		C <sub>oes</sub>	_	126	_	
Transfer Capacitance	,	C <sub>res</sub>	_	16	_	
SWITCHING CHARACTERISTICS (1	1)					
Turn-On Delay Time		<sup>t</sup> d(on)	_	74	_	ns
Rise Time	$(V_{CC}=720~Vdc,~I_{C}=10~Adc,~V_{GE}=15~Vdc,~L=300~\mu H~R_{G}=20~\Omega)$ Energy losses include "tail"	t <sub>r</sub>	_	83	_	
Turn-Off Delay Time		t <sub>d</sub> (off)	_	76	_	
Fall Time		t <sub>f</sub>	_	231	_	
Turn-Off Switching Loss		E <sub>off</sub>	_	0.55	1.33	mJ
Turn-On Delay Time	(V <sub>CC</sub> = 720 Vdc, I <sub>C</sub> = 10 Adc, V <sub>GE</sub> = 15 Vdc, L = 300 μH R <sub>G</sub> = 20 Ω, T <sub>J</sub> = 125°C) Energy losses include "tail"	<sup>t</sup> d(on)	_	66	_	ns
Rise Time		t <sub>r</sub>	_	87	_	]
Turn-Off Delay Time		td(off)	_	120	_	
Fall Time		t <sub>f</sub>	_	575	_	
Turn-Off Switching Loss		E <sub>off</sub>	_	1.49	_	mJ
Gate Charge	(V <sub>CC</sub> = 720 Vdc, I <sub>C</sub> = 10 Adc, V <sub>GE</sub> = 15 Vdc)	QT	_	31	_	nC
		Q <sub>1</sub>	_	13	_	1
		Q <sub>2</sub>	_	14	_	
NTERNAL PACKAGE INDUCTANC	E					
Internal Emitter Inductance (Measured from the emitter lead 0.25" from package to emitter bond pad)		LE	_	13		nH

Motorola IGBT Device Data

### TYPICAL ELECTRICAL CHARACTERISTICS

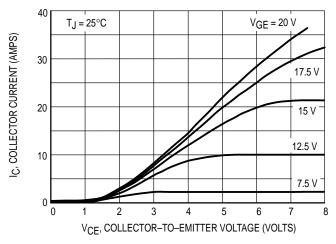


Figure 1. Output Characteristics

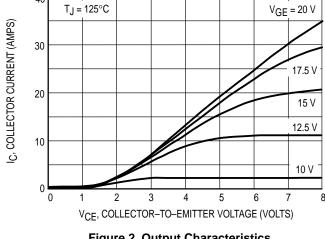


Figure 2. Output Characteristics

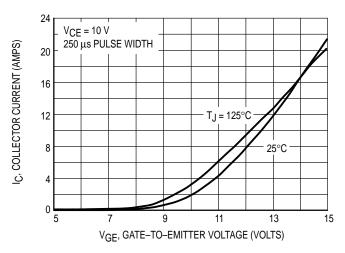


Figure 3. Transfer Characteristics

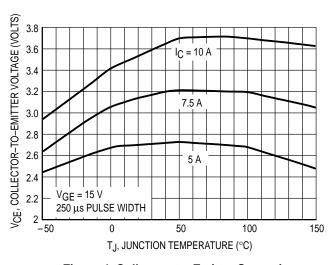


Figure 4. Collector-to-Emitter Saturation **Voltage versus Junction Temperature** 

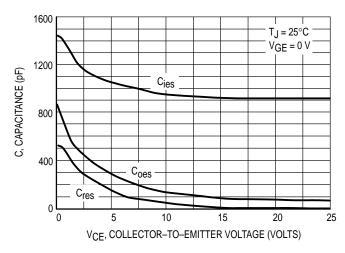


Figure 5. Capacitance Variation

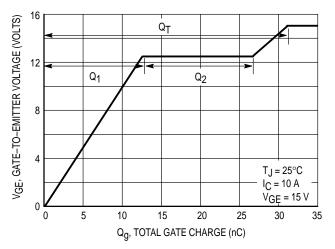


Figure 6. Gate-to-Emitter Voltage versus **Total Charge** 

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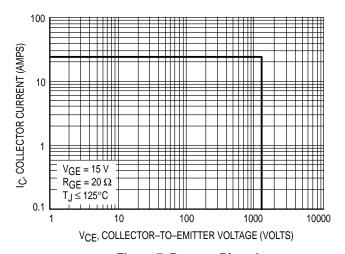


Figure 7. Reverse Biased Safe Operating Area

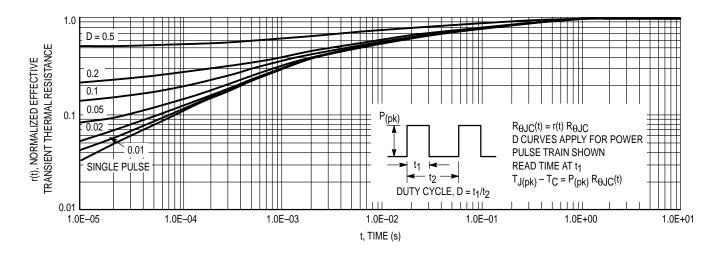
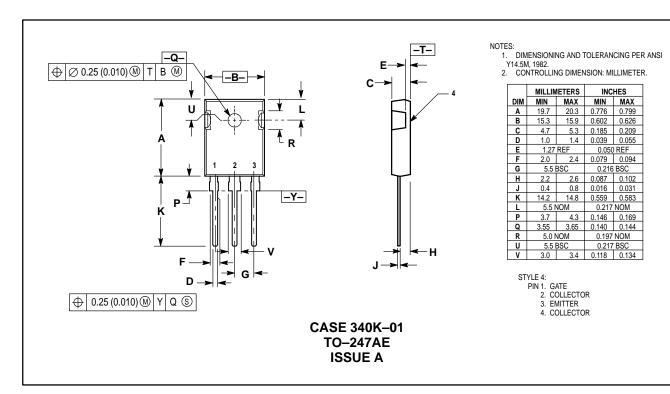


Figure 8. Thermal Response

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#### PACKAGE DIMENSIONS



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